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**AMENDMENTS TO THE SPECIFICATION**

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Please amend paragraph [0024] as follows:

[0024] FIGs. 4A to 4F[[4E]] are schematic cross sectional views of an exemplary method of fabricating an LCD device according to the present invention; and

Please amend paragraph [0025] as follows:

[0025] FIGs. 5A to 5D[[5C]] are schematic cross sectional views of another exemplary method of fabricating an LCD device according to the present invention.

Please amend paragraph [0035] as follows:

[0035] Next, an etching object layer 135 for forming a pattern may be formed on the substrate 130, as shown in Figure 4F. The etching object layer 135 may be a metal layer for forming a metal pattern, such as a gate electrode, source/drain electrodes, a gate line, a data line, a pixel electrode, and a storage electrode, or may be an insulating layer, such as SiO<sub>x</sub> or SiN<sub>x</sub>. The etching object layer may include an organic layer.